

DESCRIPTION

- With TO-3 package
- High collector-base breakdown voltage
: $V_{CBO}=350V$

APPLICATIONS

- For TV horizontal output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

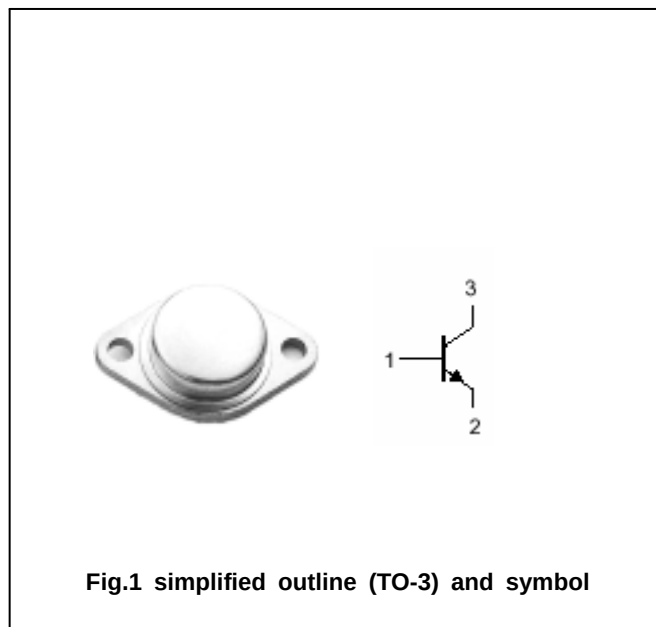


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a=^{\circ}C$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	350	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		8	A
P_C	Collector power dissipation	$T_C=25^{\circ}C$	50	W
T_j	Junction temperature		150	$^{\circ}C$
T_{stg}	Storage temperature		-55~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	CHARACTERISTICS	MAX	UNIT
$R_{\theta jc}$	Thermal resistance junction to case	1.5	$^{\circ}C/W$

SPTECH Product Specification

SPTECH Silicon NPN Power Transistors

3DD201

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA ; I _B =0	150			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	350			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A; I _B =0.5A			1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5A; I _B =0.5A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =350V; I _E =0			0.5	mA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =2A ; V _{CE} =10V	40		120	

PACKAGE OUTLINE

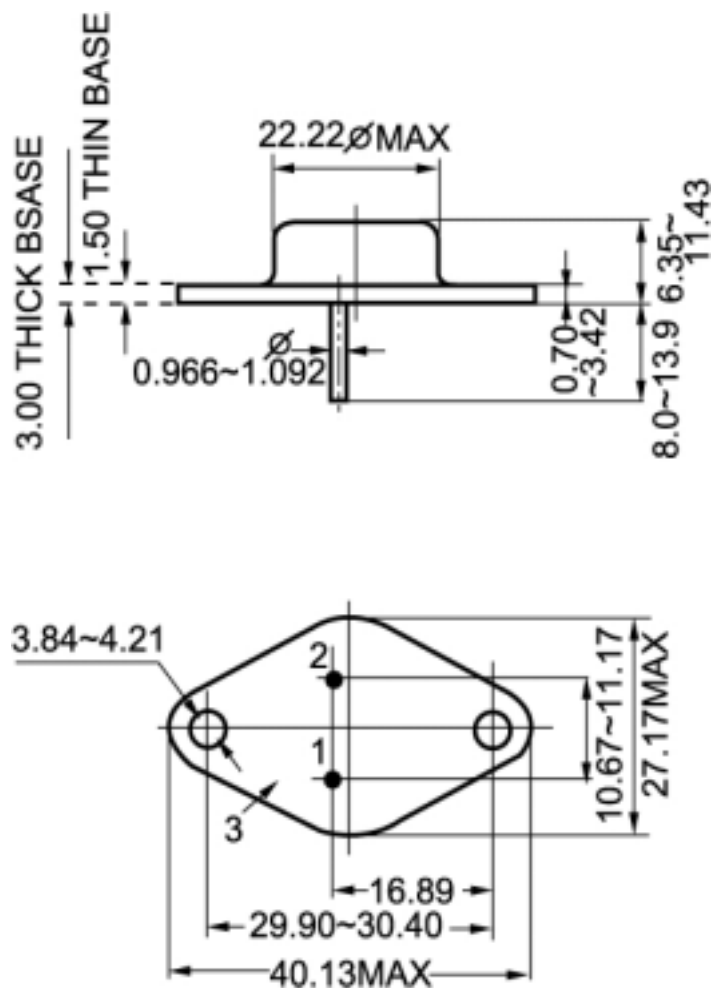


Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)